APPM/8830/FEP/LPCvD/PJS ATTY DKT. No.:

U.S. SERIAL NO.: UNKNOWN FILED:

APPLICANT: TITLE:

 $\Gamma$ 

**HEREWITH** 

APPLIED MATERIALS
NOVEL GATE ELECTRODE DOPANT ACTIVATION METHOD

CONF. No.: UNKNOWN

FOR SEMICONDUCTOR MANUFACTURING

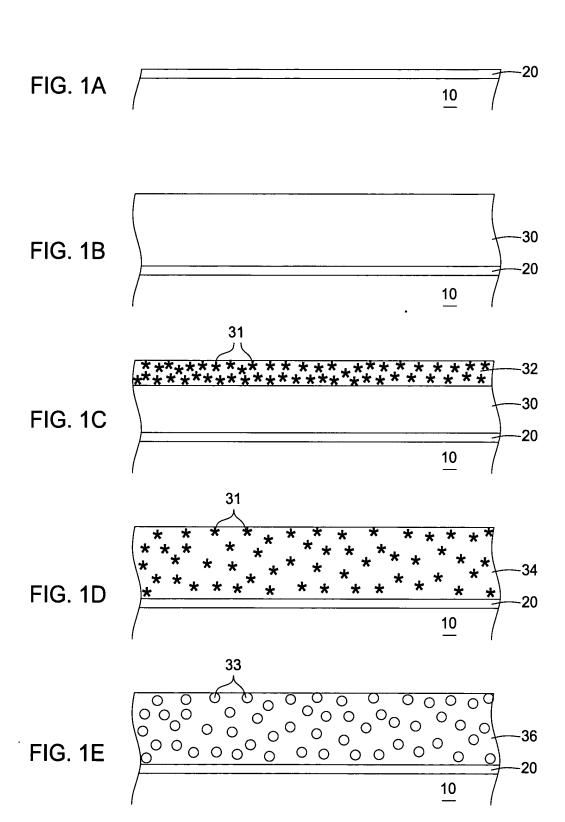
INVENTOR: YI MA, ET AL.

EXPRESS MAIL No.: EV351032147US

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APPM/8830/FEP/LPCvD/PJS ATTY DKT. No.:

U.S. SERIAL NO.: UNKNOWN FILED: **HEREWITH** 

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CONF. No.: UNKNOWN

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INVENTOR: YI MA, ET AL. EXPRESS MAIL No.: EV351032147US

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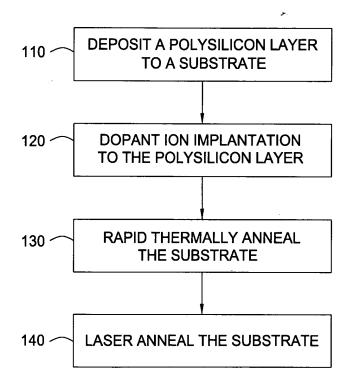


FIG. 2

ATTY DKT. NO.: APPM/8830/FEP/LPCVD/PJS U.S. SERIAL NO.: UNKNOWN

FILED:

HEREWITH

CONF. No.: UNKNOWN

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INVENTOR:

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